WEST Search History

Hide Items Restore Clear Cancel

DATE: Wednesday, August 31, 2005

Hide?	<u>Set</u> Name	Query	<u>Hit</u> Count				
DB=PGPB, USPT; PLUR=YES; OP=OR							
Г	L6	L3 and porous.clm.	96				
Γ	L5	L3 not L4	382				
Γ	L4	L2 and porous and anodiz\$6	102				
Γ	L3	438/404,409.ccls.	457				
Γ	L2	438/404-412,424-426.ccls.	2956				
	DB=PG	SPB, USPT, USOC, EPAB, JPAB, DWPI, TDBD; PLUR=YES; OP=OR	•				
Γ	L1	porous and anodiz\$6 and ((dielectric with isolation) or SOI) and (via\$1 or trench\$2)	339				

END OF SEARCH HISTORY

ŧ



Home | Login | Logout | Access Information | Ale

Welcome United States Patent and Trademark Office

Advano	ed Search	BROWSE	SEARCH	IEEE XPLORE GUIDE
©	OPTION 1 Enter keywords or phrases, select fields, and se	rs years	,	Publications Select publications IEEE Periodicals
	AND ▼ in A	Il Fields Il Fields ↓ Il Fields ↓		✓ IEEE Periodicals ✓ IEEE Conference Proceedings ✓ IEE Conference Proceedings
		⊻		IEEE Standards
©	OPTION 2 Enter keywords, phrases, or a Boolean expressi	on	1	Other Resources (Available for Purchase) Value
	porous <and> isolation <a anodization <or> anodized</or></a </and>		<u>.</u>	Select date range Search latest content update (29 Aug 200 From year All to Present
			,	Display Format
	» Note: You may use the search operators <and> o without the start and end brackets <>.</and>	r <0r>		Citation & Abstract
	» Learn more about <u>Field Codes, Search Examples</u>	, and <u>Search Operators</u>	,	Organize results Maximum 100 Display 25 results per page Sort by Relevance
				In Descending ✓ order

Indexed by

© Copyright 2005 IE

1

IEEE Xplore®

Home | Login | Logout | Access Information | Ate

	RELEASE 2.1	Welcome United States Patent and Trademark Office						
Search Resul	ts			BROWSE	SEARCH	IEEE XPLORE GUIDE		
Your search n	porous <and> isolation <and> (a natched 5 of 1229994 documents. f 100 results are displayed, 25 to a</and></and>						⊠ e-mail	
» Search Opti	ons							
View Session	<u>History</u>	Modif	y Search			•		
New Search		((porous <and> isolation <and> (anodize <or> anodization <or> anodized))<in>metad</in></or></or></and></and>						
		\sqcap	Check to search	only within this re	sults set			
» Key		Displa	y Format:	© Citation	Citation & Abstra	ct		
IEEE JNL	IEEE Journal or Magazine				•			
IEE JNL	IEE Journal or Magazine	Select	Article Infor	mation				
IEEE CNF	IEEE Conference Proceeding	г	1. Effective	crosstalk isolatio	on through p ⁺ SI substra	tes with semi-insulating porc	ous Si	
IEE CNF	IEE Conference Proceeding	Han-Su Kim; Jenkins, K.A.; Ya-Hong Xie;						
IEEE STD	IEEE Standard		Electron Device Letters, IEEE Volume 23, Issue 3, March 2002 Page(s):160 - 162					
				ject Identifier 10.1				
			AbstractP	ius References	Full Text: <u>PDF</u> (201 KB)	IEEE JNL		
	• .	Γ	Imai, K.; U Electron D	Inno, H.; Devices, IEEE Trai	•	echnology and its applicatio	n to LSI's	
					F(752 KB) IEEE JNL			
		Γ.	Zorinsky, i 1986 Inter Volume 32	E.J.; Spratt, D.B.; mational Electron 2, 1986 Page(s):4	Virkus, R.L.; Devices Meeting	s silicon SOI technology		
			7.1301.1301.	<u></u>				
		Γ	the micro Hoon-Sun Microproc 29-31 Oct	-well g Choi; Chang-Ta esses and Nanote . 2003 Page(s):32	neg Seo; Young-Min Kim; v echnology Conference, 200 6 - 327	ick thermal isolation layer an Jang-Kyoo Shin; Pyung Choi; J 03. Digest of Papers. 2003 Inte	long-Hyun Lee	
			MUSITACIF	ius į ruli Text. <u>FD</u>	<u>F(</u> 256 KB) IEEE CNF			
		T:	Tsybesko Device Re 24-26 Jun Digital Ob	v, L.; Hirschman, I esearch Conference e 1996 Page(s):19 ject Identifier 10.1	109/DRC.1996.546416	uchet, P.M.;	·	
			<u>AbstractPl</u>	lus Full Text: <u>PD</u>	<u>F(</u> 148 KB) IEEE CNF			

Help Contact Us Privac

Indexed by Inspec

ì

© Copyright 2005 IE